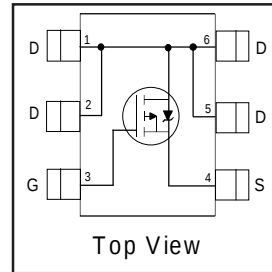


IRF5800

HEXFET® Power MOSFET

- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Low Gate Charge



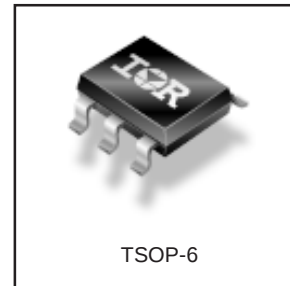
$$V_{DS} = -30V$$

$$R_{DS(on)} = 0.085\Omega$$

Description

These P-channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications.

The TSOP-6 package with its customized leadframe produces a HEXFET® power MOSFET with $R_{DS(on)}$ 60% less than a similar size SOT-23. This package is ideal for applications where printed circuit board space is at a premium. Its unique thermal design and $R_{DS(on)}$ reduction enables a current-handling increase of nearly 300% compared to the SOT-23.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-30	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-4.0	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-3.2	
I_{DM}	Pulsed Drain Current ①	-32	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.0	W
$P_D @ T_A = 70^\circ C$	Power Dissipation	1.3	
	Linear Derating Factor	0.016	W/°C
E_{AS}	Single Pulse Avalanche Energy④	20.6	mJ
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

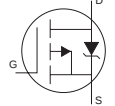
Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	62.5	°C/W

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.02	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.085 0.150	Ω	$V_{GS} = -10V, I_D = -4.0A$ ② $V_{GS} = -4.5V, I_D = -3.0A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	—	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	3.5	—	—	S	$V_{DS} = -10V, I_D = -4.0A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0 -5.0	μA	$V_{DS} = -24V, V_{GS} = 0V$ $V_{DS} = -24V, V_{GS} = 0V, T_J = 70^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage Gate-to-Source Reverse Leakage	—	—	-100 100	nA	$V_{GS} = -20V$ $V_{GS} = 20V$
Q_g	Total Gate Charge	—	11.4	17	nC	$I_D = -4.0A$ $V_{DS} = -16V$ $V_{GS} = -10V$ ②
Q_{gs}	Gate-to-Source Charge	—	2.3	—		
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	2.2	—		
$t_{d(on)}$	Turn-On Delay Time	—	11.4	17	ns	$V_{DD} = -15V, V_{GS} = -10V$ $I_D = -1.0A$ $R_G = 6.0\Omega$ $R_D = 15\Omega$, ②
t_r	Rise Time	—	11	17		
$t_{d(off)}$	Turn-Off Delay Time	—	24	36		
t_f	Fall Time	—	14	20		
C_{iss}	Input Capacitance	—	535	—	pF	$V_{GS} = 0V$ $V_{DS} = -25V$ $f = 1.0MHz$
C_{oss}	Output Capacitance	—	94	—		
C_{rss}	Reverse Transfer Capacitance	—	68	—		

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-32		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -2.0A, V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	19	28	ns	$T_J = 25^\circ\text{C}, I_F = -2.0A$
Q_{rr}	Reverse Recovery Charge	—	16	24	nC	$di/dt = -100A/\mu s$ ②

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

③ Surface mounted on FR-4 board, $t \leq 5sec$.

④ Starting $T_J = 25^\circ\text{C}$, $L = 2.5mH$
 $R_G = 25\Omega$, $I_{AS} = -4.0A$. (See Fig 10)

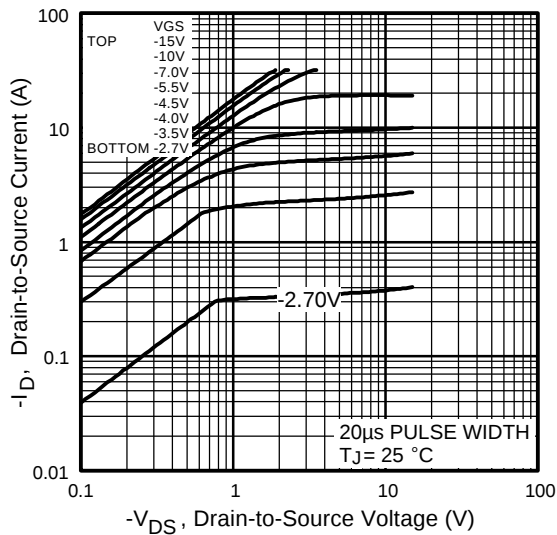


Fig 1. Typical Output Characteristics

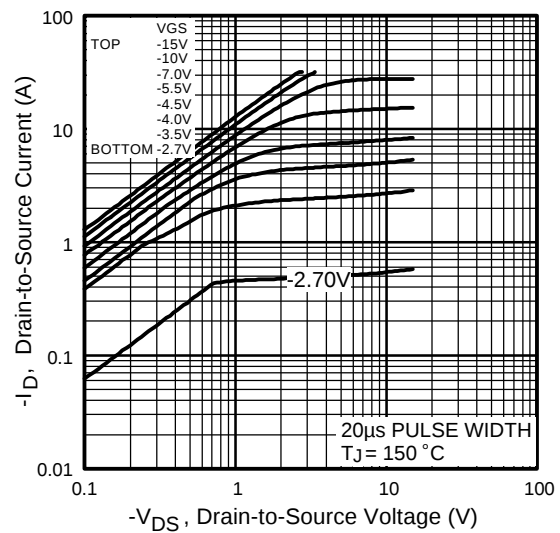


Fig 2. Typical Output Characteristics

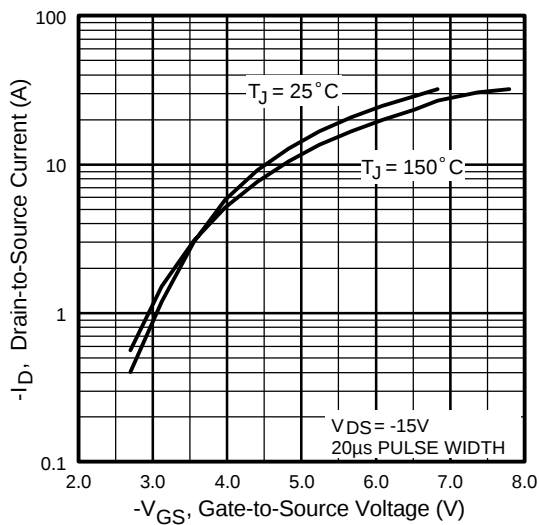


Fig 3. Typical Transfer Characteristics

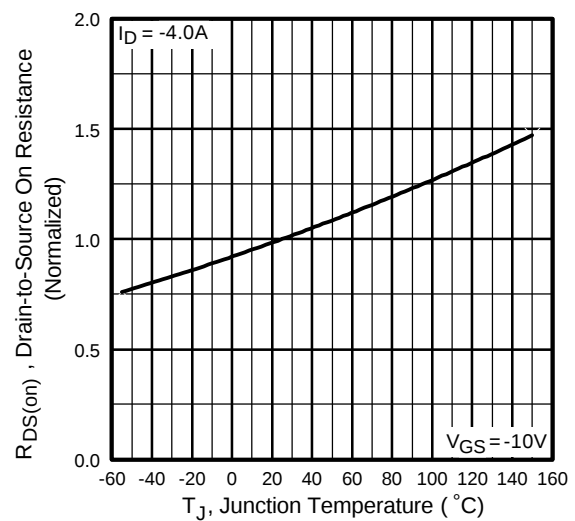


Fig 4. Normalized On-Resistance Vs. Temperature

IRF5800

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IR Rectifier

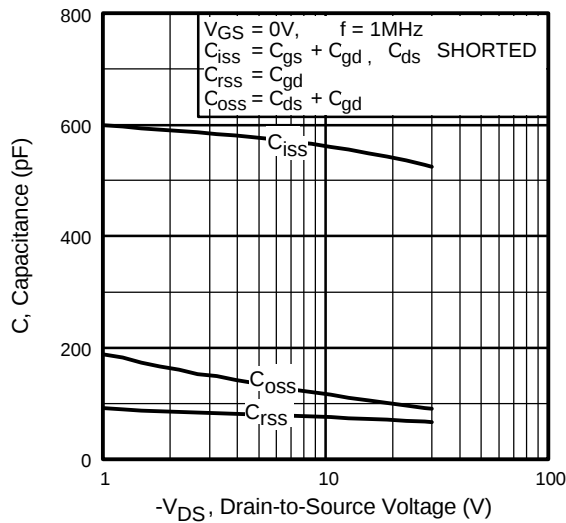


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

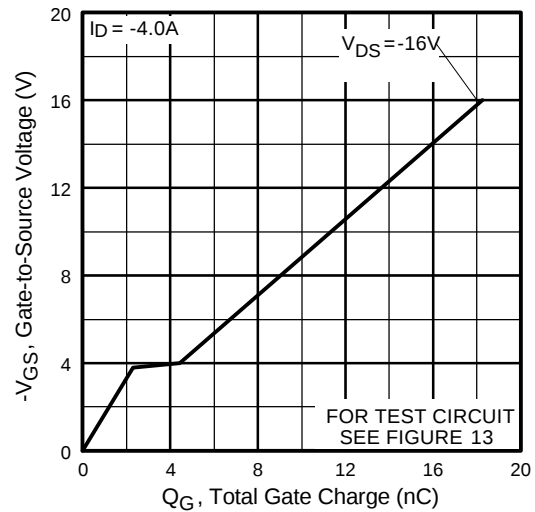


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

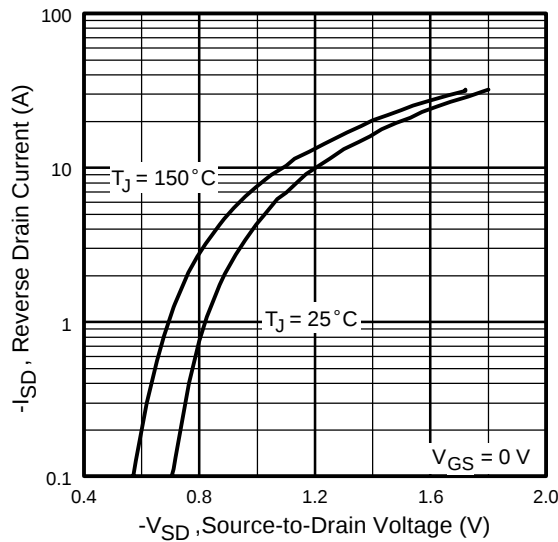


Fig 7. Typical Source-Drain Diode Forward Voltage

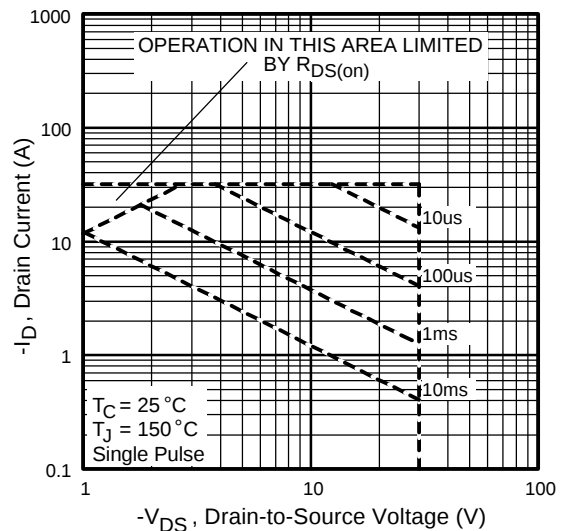


Fig 8. Maximum Safe Operating Area

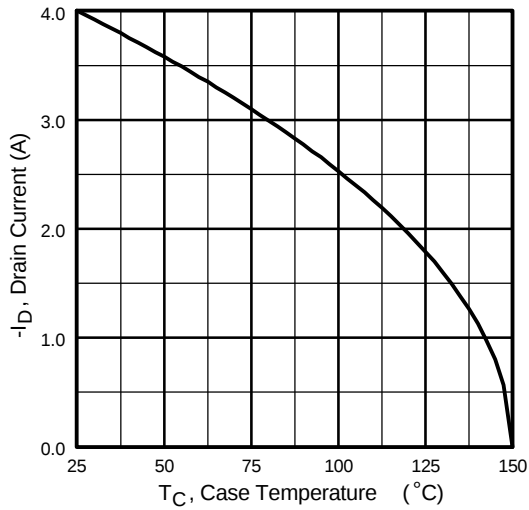


Fig 9. Maximum Drain Current Vs. Case Temperature

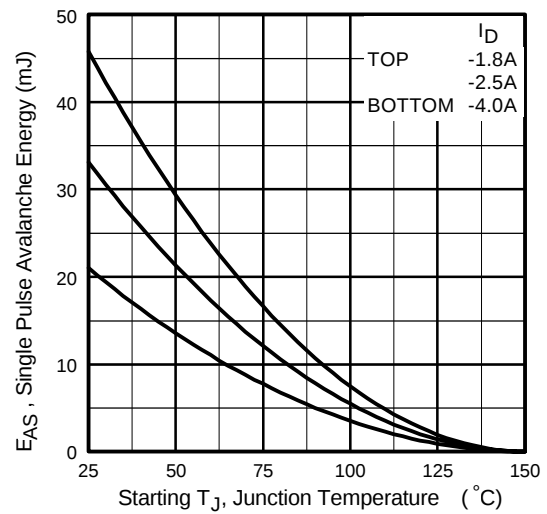


Fig 10. Maximum Avalanche Energy Vs. Drain Current

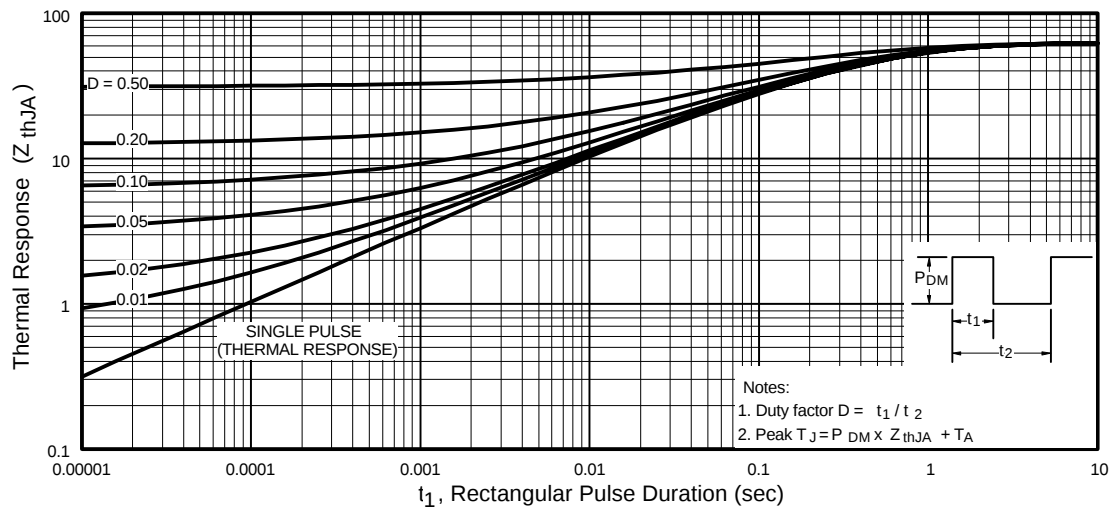


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

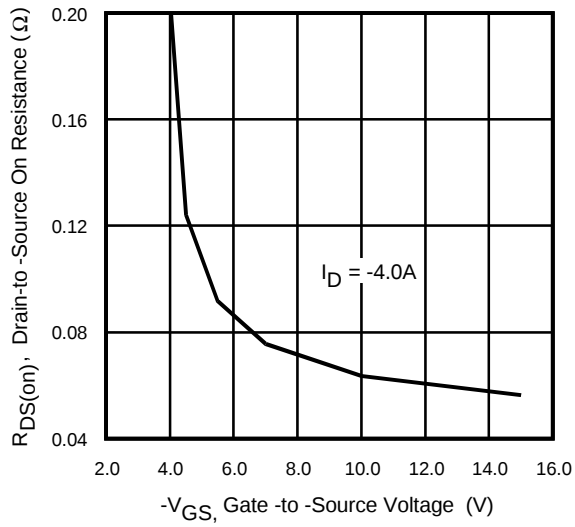


Fig 12. Typical On-Resistance Vs. Gate Voltage

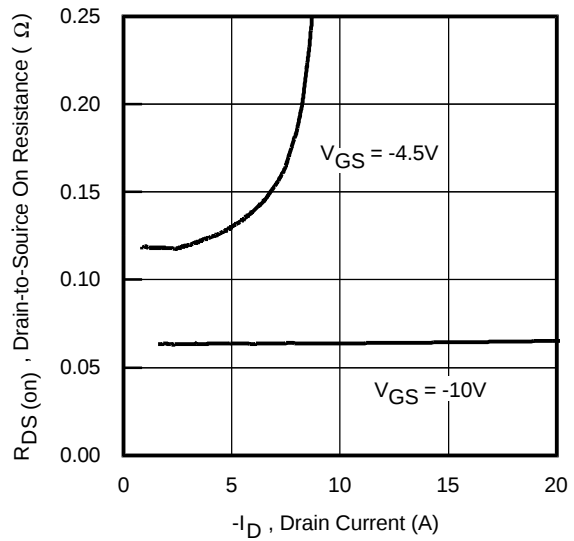
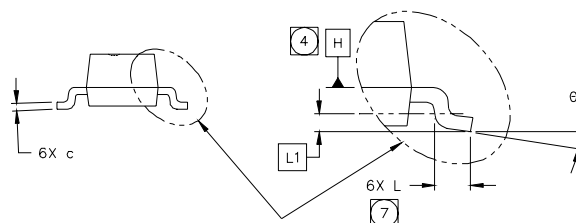
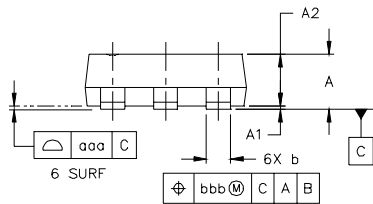
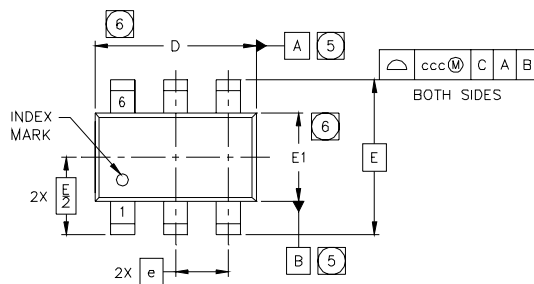


Fig 13. Typical On-Resistance Vs. Drain Current

TSOP-6 Package Outline

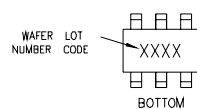
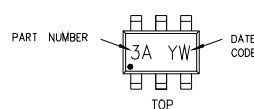


SYMBOL	MO-193AA DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	.0433
A1	0.01	---	0.10	.0004	---	.0039
A2	0.80	0.90	1.00	.0315	.0354	.0393
b	0.25	---	0.50	.0099	---	.0196
c	0.10	---	0.26	.004	---	.010
D	2.90	3.00	3.10	.115	.118	.122
E	2.75 BSC			.108 BSC		
E1	1.30	1.50	1.70	.052	.059	.066
e	1.00 BSC			.039 BSC		
L	0.20	0.40	0.60	.0079	.0157	.0236
L1	0.30 BSC			.0118 BSC		
θ	0°	---	8°	0°	---	8°
aaa	0.10			.004		
bbb	0.15			.006		
ccc	0.25			.010		

TSOP-6 Part Marking Information

EXAMPLE: THIS IS AN SI3443DV

WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER EXAMPLES:

3A = SI3443DV

DATE CODE EXAMPLES:

YW = 9603 = 6C

YW = 9632 = FF

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

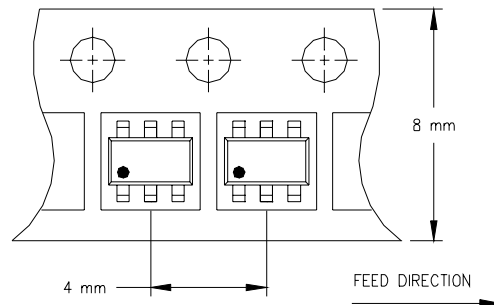
WW = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

IRF5800

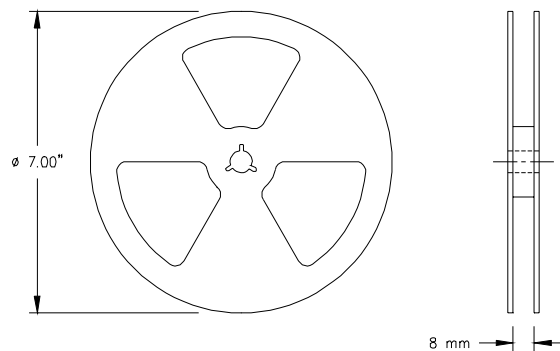
International
IR Rectifier

TSOP-6 Tape & Reel Information



NOTES:

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.

International
IR Rectifier

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IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR JAPAN: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086

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IR TAIWAN: 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan Tel: 886-2-2377-9936

Data and specifications subject to change without notice. 2/2000

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